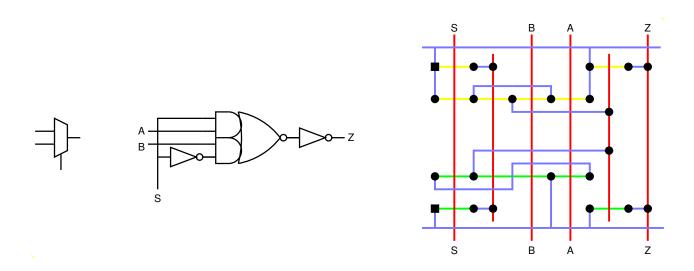
# Alternative Cell Design Strategy

### Gate Matrix Style

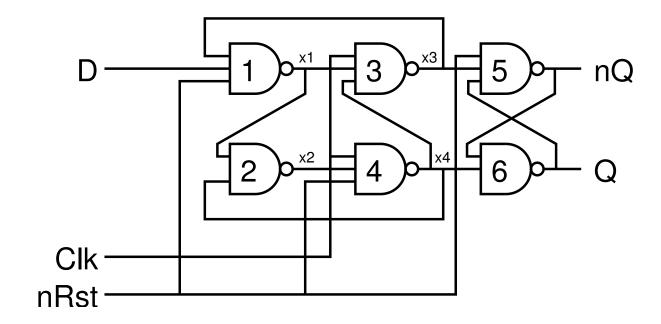
The circuit is created as a matrix of intersecting transistor diffusion rows and polysilicon columns.

A simple example is the two input multiplexor we saw earlier. We align transistors on their common gate connections (as for *line of diffusion* designs), but here we allow multiple transistors to use the same polysilicon column.

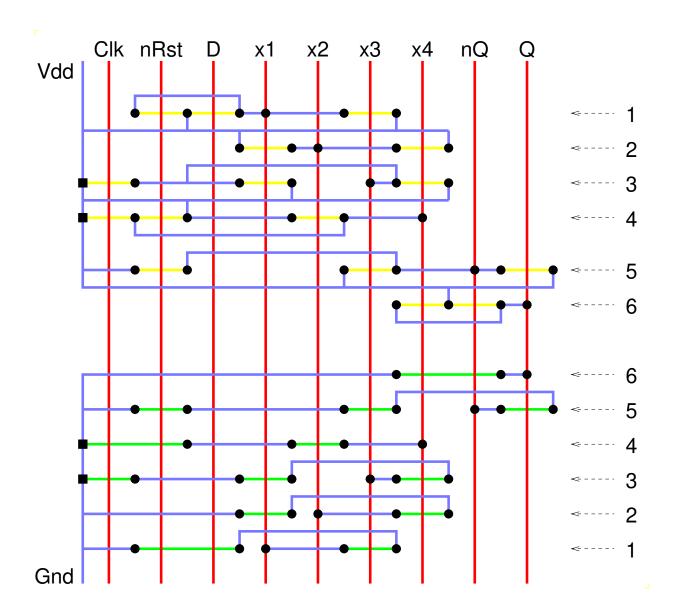


## Gate Matrix Style

The layout of a standard six NAND gate d-type should illustrate the style more completely.



Here each NAND gate is allocated a different pair of rows in the layout (further optimization of this circuit is possible).



# Cell Design Choices

#### • Line of Diffusion – Euler Path

The line of diffusion approach to cell design, backed up by investigation of Euler paths, leads to efficient layout of small cells.

#### • Gate Matrix<sup>1</sup>

Where cells are more complex and in particular when there are multiple transistors sharing a common gate connection, gate matrix design will often give more efficient use of area.

- Complex Standard Cells
  - - Mux, D-Type, Full Adder etc
    - consider impact of tall gate matrix cells on space efficiency in simple cells.
- Full Custom Cells
  - - Efficient sub-circuit design.e.g. Full custom ALU bitslice.

<sup>&</sup>lt;sup>1</sup>note that partial Euler paths play an important part in efficient Gate Matrix design.